

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in this divisional application:

Claim 1-7 (Canceled)

8. (Original) A semiconductor device formed on a semiconductor substrate comprising active regions, bit lines, first conductive plugs, second conductive plugs, and word lines and characterized by a minimum line width "F", and a minimum spacing width, and a cell size of less than $8F^2$ comprising:

parallel rows of active regions of minimum line width and a basic rectangular shape arranged in the semiconductor substrate with adjacent active regions being separated by the minimum spacing width;

parallel columns of word lines of minimum line width arranged in a direction perpendicular to the parallel rows of active regions with adjacent word lines being separated by the minimum spacing, the word lines being positioned to that two word lines cross each active region leaving three uncovered portions, a center portion and two end portions, in each active region; an insulating film formed between the word lines;

first conductive plugs positioned between adjacent bits lines and contacting an uncovered portion of an active region;

an interlayer insulating film formed above the first conductive plugs;

bit line contact plugs positioned above, partially overlapping, and in contact with the first conductive plugs; and

parallel rows of bit lines of minimum line width arranged in a direction parallel to the parallel rows of active regions with adjacent bit lines being separated by the minimum spacing, the bit lines being positioned to partially overlap and contact the bit line contact plugs.

Claims 9-15 (Canceled)

16. (Original) A DRAM device comprising a plurality of DRAM cells formed on a semiconductor substrate, each DRAM cell being characterized by a minimum line width, F,

and a minimum spacing, S , wherein the area of a single DRAM cell is less than $8F^2$ comprising:

active regions in the semiconductor substrate, the active regions being characterized by the minimum width F and a length of at least about $5F$, wherein the active regions are arranged in parallel rows and separated from adjacent active regions by the minimum spacing S , and further wherein active regions in adjacent rows are offset from each other in a longitudinal direction;

word lines, each word line being characterized by the minimum width F , wherein each word line is parallel to, and separated by the minimum spacing S from, adjacent word lines, and further wherein the word lines are perpendicular to the rows of active regions;

an insulating film formed over the word lines; first conductive plugs extending through the insulating film between adjacent word lines and making contact to portions of the active regions between adjacent word lines;

an interlayer insulating film formed over the first conductive plugs;

second conductive plugs extending through the interlayer insulating film, the second conductive plugs partially overlapping and contacting the first conductive plugs; and bit lines that partially overlap and make contact with the second conductive plugs, the bit lines being characterized by the minimum line width F , wherein adjacent bit lines are parallel and separated by the minimum spacing S , and further wherein the bit lines are oriented in a direction parallel to the rows of active regions.